	Hits	Search Text	DBs
17	46	((mask$3 or photomask or reticle) same (resist or photoresist or photosensitive or (radiation near5 sensitive)) same (substrate or wafer or workpiece)) and (((pattern$4 near3 material) or conductive or metallic or metal$4 or Au or Ag or Cu or film) same (deposit$4 or coat$4 or layer or form$3) same (selective$3 or (mask$3 same opening)) same (plural$4 or multiple)) and ((heat$4 or anneal$7 or bak$4) same simultaneous$3 same (strip$5 or remov$4 or etch$4 or detach$5) same (mask or pattern) same (workpiece or substrate or wafer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
18	7	(mask$3 or photomask or reticle) and (((pattern$4 near3 material) or resist or photoresist or (radiation near3 sensitive)) same (deposit$4 or coat$4 or layer or form$3) same (selective$3 or (mask$3 same opening))) and ((heat$4 or anneal$7 or bak$4) near12 simultaneous$3 near14 (strip$5 or remov$4 or etch$4 or detach$5) near12 (mask or pattern) near16 (workpiece or substrate or wafer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
19	160	((heat$4 or anneal$7 or bak$4) near8 simultaneous$3 near9 (strip$5 or remov$4 or etch$4 or detach$5) near9 (mask or pattern or photoresist or resist))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
20	126	((heat$4 or anneal$7 or bak$4) near8 simultaneous$3 near9 (strip$5 or remov$4) near9 (mask or pattern or photoresist or resist))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
21	31	((heat$4 or anneal$7 or bak$4 or cur$4) near14 simultaneous$3 near12 (strip$5 or remov$4) near14 (mask or pattern) near9 (photoresist or resist or polylmer$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
22	85	((pyrolysis or pyr$1oly$4 or sublimat$5) near16 (mask or pattern) near9 (photoresist or resist))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB